



DMN63D1LDW

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ V _{GS} = 10V	250mA
000	3Ω @ V _{GS} = 5V	250MA

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

SOT363

Top View

Applications

- Motor Control
- Power Management Functions

Features

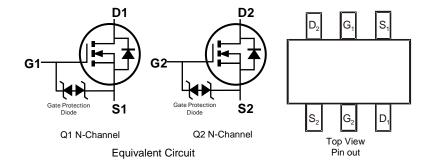
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Ordering Information (Note 4)

ESD Protected Gate

Part Number	Case	Packaging
DMN63D1LDW-7	SOT363	3000/Tape & Reel
DMN63D1LDW-13	SOT363	10000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:

Date Code K	ey		D ₂ G ₁ 1D3 M WA E S ₂ G ₂		1D3 = Product Type Marking Code YM = Date Code Marking \overline{Y} or \underline{Y} = Year (ex: B = 2014) M = Month (ex: 9 = September)							
Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	E	F	G	Н	I	J	K	L	М
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		Ι _D	250 200	mA	
Maximum Continuous Body Diode Forward Curren	t (Note 6)	ls	0.5	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	6) (Note 6	I _{DM}	1.2	A	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	414	°C/W
Total Power Dissipation (Note 6)		PD	390	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	324	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		-	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.6	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static Drain-Source On-Resistance		_	—	2.0	0	$V_{GS} = 10V, I_D = 0.5A$
	R _{DS(ON)}		—	3.0	12	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80	-	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V _{SD}		0.75	1.1	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	30	—	pF	
Output Capacitance	Coss		4.2	—	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss		2.9	—	pF	1 = 1.00012
Gate Resistance	Rg	_	133	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg	-	304		рС	
Gate-Source Charge	Q _{gs}	—	203	—	рС	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{gd}	_	84	—	рС	I _D = 250mA
Turn-On Delay Time	t _{D(ON)}	_	3.9	—	ns	
Turn-On Rise Time	t _R		3.4	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}	_	15.7	—	ns	$R_{G} = 25\Omega, I_{D} = 200 \text{mA}$
Turn-Off Fall Time	tF	_	9.9	—	ns	

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

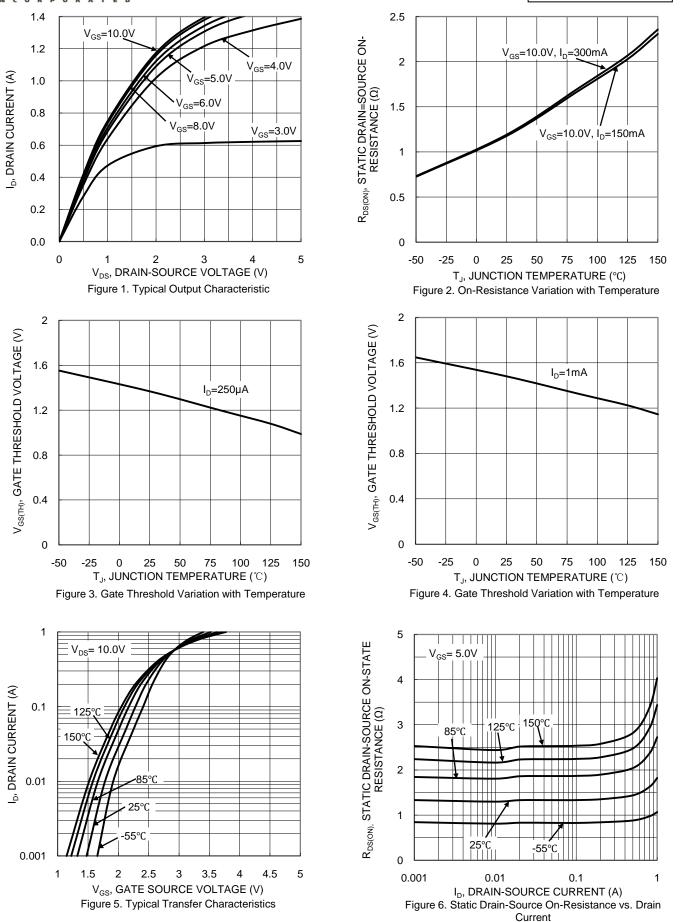
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



DMN63D1LDW



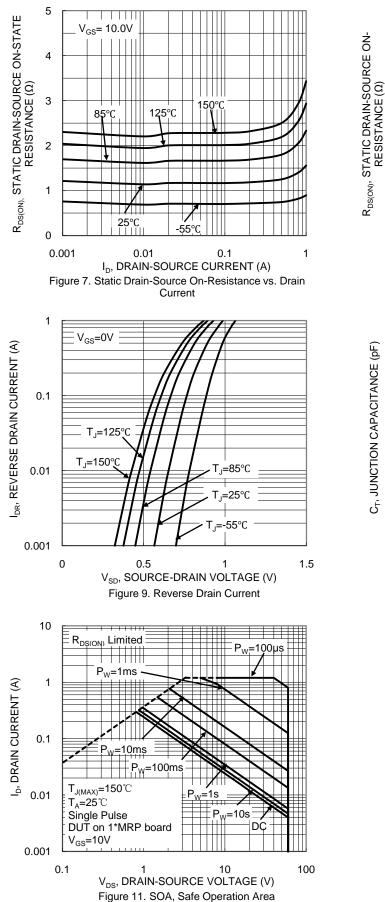
NEW PRODUCT

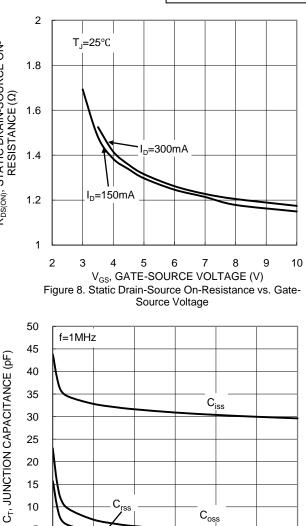
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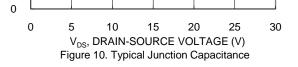


NEW PRODUCT

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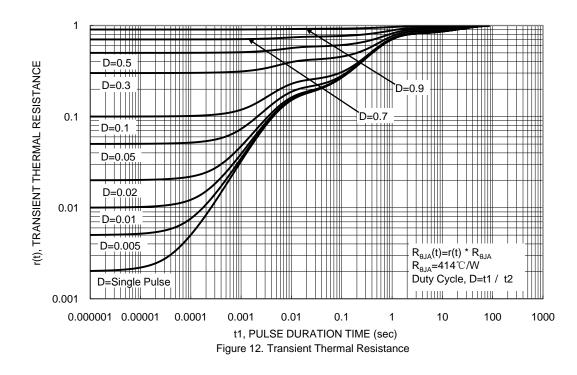






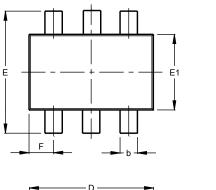
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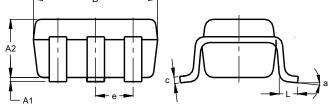




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



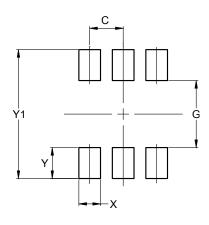


SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	1.00				
b	0.10	0.30	0.25				
С	0.10	0.22	0.11				
D	1.80	2.20	2.15				
E	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0).650 B	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а		8°					
All	All Dimensions in mm						



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500

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